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Data Sheet

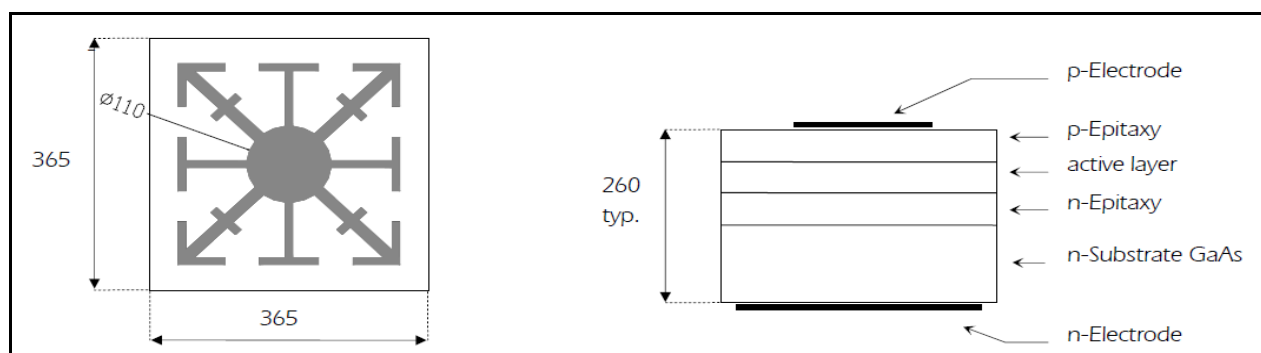
Preliminary

LED Chip Infrared

EOLC-1140-17

Rev. 01, 2017

Radiation	Type	Electrodes
Infrared	InGaAs/GaAs, MQW	P (anode) up



Chip thickness: typ. 260±30 µm, bonding pad Ø110±15 µm, electrodes / metallization - Au alloy

Optical and Electrical Characteristics

T_{amb} = 25°C, unless otherwise specified

Parameter	Test cond.	Symbol	Min	Typ	Max	Unit
Forward voltage	I _F =20 mA	V _F		1.1	1.3	V
Forward voltage	I _F =100 mA	V _F		1.2	1.4	V
Reverse current	V _R =5 V	I _R			10	µA
Radiant power*	I _F =50 mA	Φ _e	2.5	3.5		mW
Radiant intensity*	I _F =100 mA	Φ _e	0.7	1		mW/sr
Peak wavelength	I _F =100 mA	λ _p	1120	1140	1160	nm
FWHM	I _F =20 mA	Δλ _{0.5}		70		nm
Switching time	I _F =100 mA	t _r , t _f		20		ns

*Measured on bare chip on TO-18 header

Packing

Chips on adhesive film with wire-bond side top

Art. No. xxx xxx



We reserve the right to make changes to improve technical design and may do so without further notice. Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer.